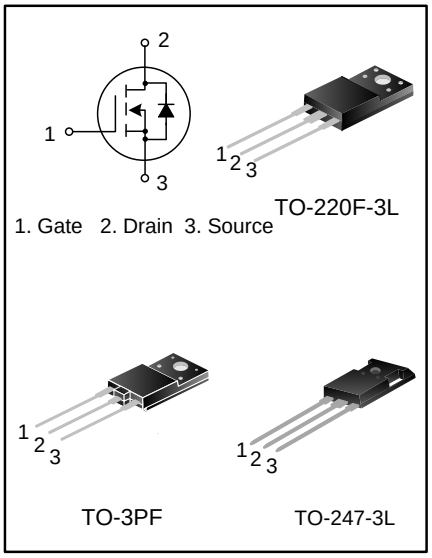
4A, 1500V N-CHANNEL MOSFET

GENERAL DESCRIPTION

SVF4N150PF(P7)(F) is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ high-voltage planar VDMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in power supplies.



FEATURES

- 4A, 1500V, $R_{DS(on)(typ)}$=5.0Ω@V_{GS}=10V
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing
SVF4N150PF	TO-3PF	4N150	Pb free	Tube
SVF4N150P7	TO-247-3L	4N150P7	Pb free	Tube
SVF4N150F	TO-220F-3L	SVF4N150F	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Characteristics		Symbol	Ratings			Unit
			SVF4N150PF	SVF4N150P7	SVF4N150F	
Drain-Source Voltage		V_{DS}	1500			V
Gate-Source Voltage		V_{GS}	±30			V
Drain Current	T_C=25°C	I_D	4.0			A
	T_C=100°C		2.5			
Drain Current Pulsed		I_{DM}	16			A
Power Dissipation(T_C=25°C)		P_D	73	160	39	W
-Derate above 25°C			0.49	1.28	0.3	W/°C
Single Pulsed Avalanche Energy(Note 1)		E_{AS}	485			mJ
Operation Junction Temperature Range		T_J	-55～+150			°C
Storage Temperature Range		T_{stg}	-55～+150			°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings			Unit
		SVF4N150PF	SVF4N150P7	SVF4N150F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.7	0.78	3.17	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	50	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	1500	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=1500V, V_{GS}=0V	--	--	10.0	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	--	--	±500	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=250μA	3.0	--	5.0	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=1.3A	--	5.0	6.5	Ω
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V, f=1.0MHZ	--	1034	--	pF
Output Capacitance	C_{oss}		--	91	--	
Reverse Transfer Capacitance	C_{rss}		--	12	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=750V， I_D=4A， R_G=25Ω (Note2,3)	--	25	--	ns
Turn-on Rise Time	t_r		--	51	--	
Turn-off Delay Time	$t_{d(off)}$		--	86	--	
Turn-off Fall Time	t_f		--	46	--	
Total Gate Charge	Q_g	V_{DS}=1200V, I_D=4A, V_{GS}=10V (Note 2,3)	--	40	--	nC
Gate-Source Charge	Q_{gs}		--	8.7	--	
Gate-Drain Charge	Q_{gd}		--	23	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction	--	--	4.0	A
Pulsed Source Current	I_{SM}	Diode in the MOSFET	--	--	16	
Diode Forward Voltage	V_{SD}	I_S=4.0A,V_{GS}=0V	--	--	1.4	V
Reverse Recovery Time	T_{rr}	I_S=4.0A,V_{GS}=0V,dI_F/dt=100A/μs	--	373	--	ns
Reverse Recovery Charge	Q_{rr}	(Note 2)	--	2.4	--	μC

Notes:

1. L=79mH, I_{AS}=3.4A, V_{DD}=100V, R_G=25Ω, starting TB_{JB}=25°C;
2. Pulse Test: Pulse width ≤300μs,Duty cycle≤2%;
3. Essentially independent of operating temperature..

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

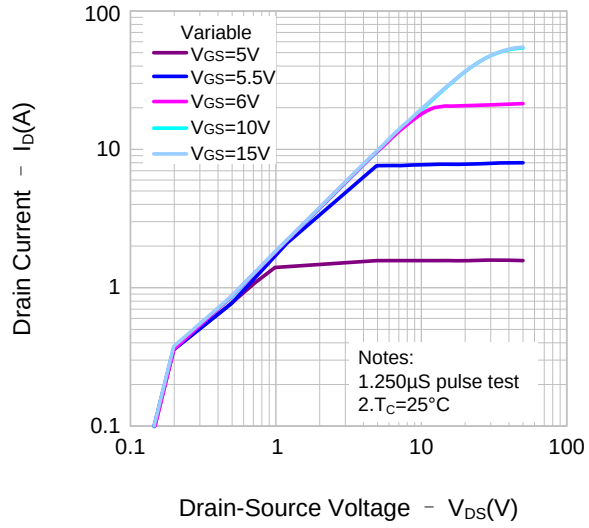


Figure 2. Transfer Characteristics

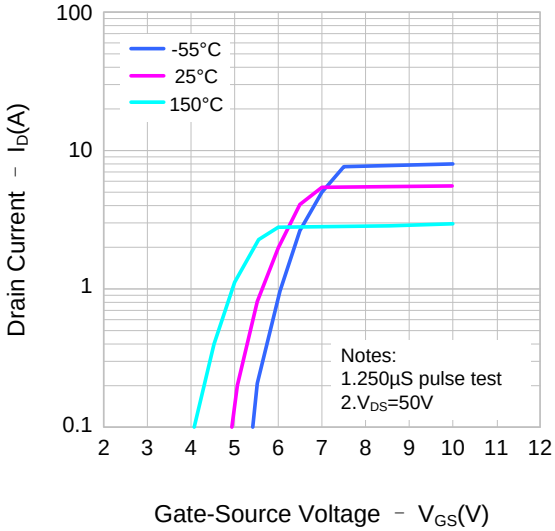


Figure 3. On-Resistance Variation vs. Drain Current

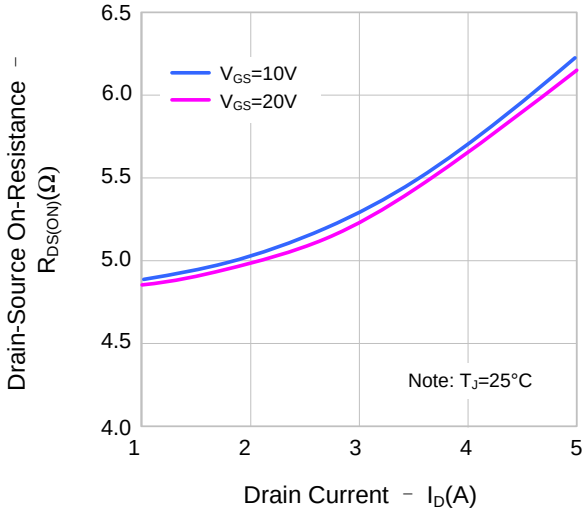
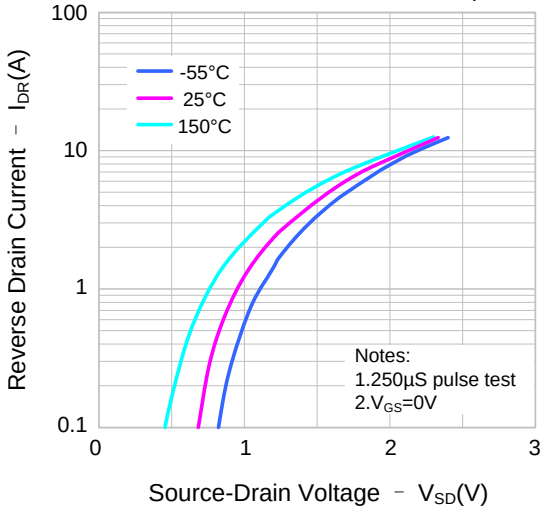


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS(continued)

Figure 5. Capacitance Characteristics

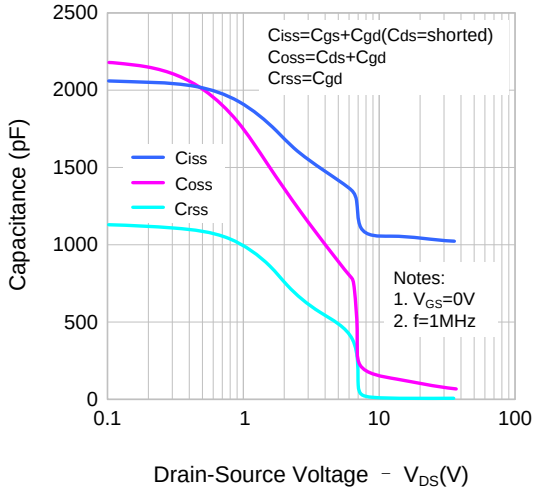


Figure 6. Gate Charge Characteristics

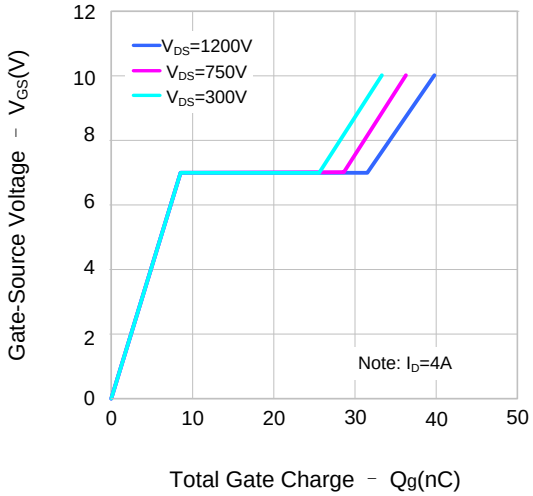


Figure 7. Breakdown Voltage Variation vs. Temperature

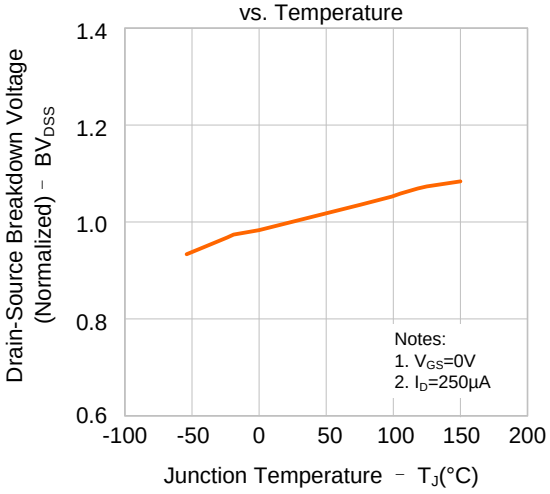


Figure 8. On-Resistance Variation vs.Temperature

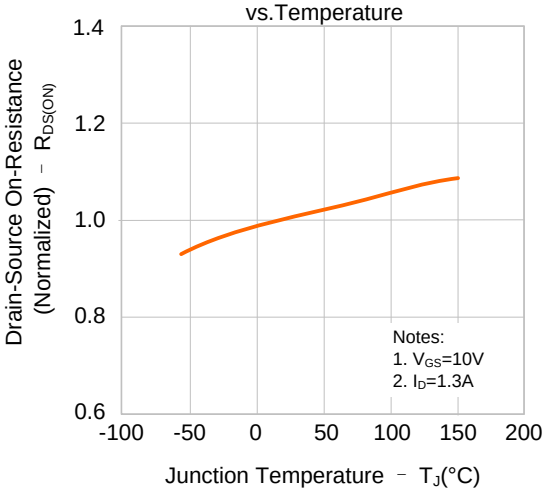


Figure 9-1. Max. Safe Operating Area(SVF4N150PN)

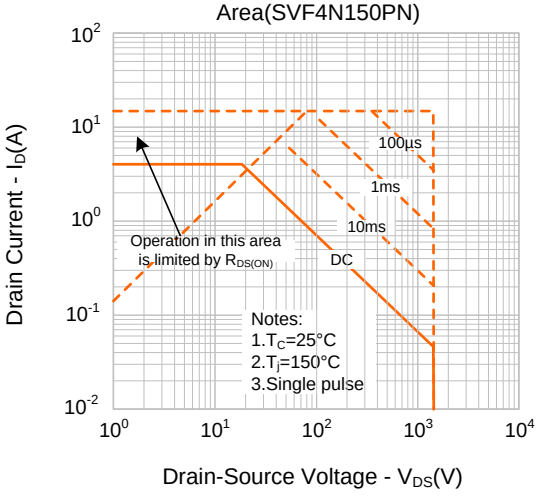
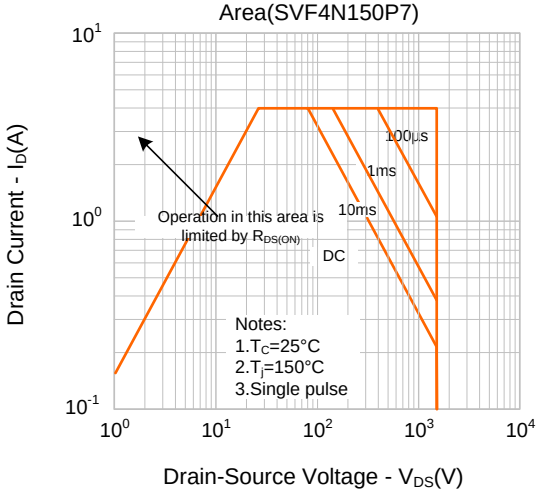


Figure9-2. Max. Safe Operating Area(SVF4N150P7)



TYPICAL CHARACTERISTICS(continued)

Figure 9-3. Max. Safe Operating Area(SVF4N150F)

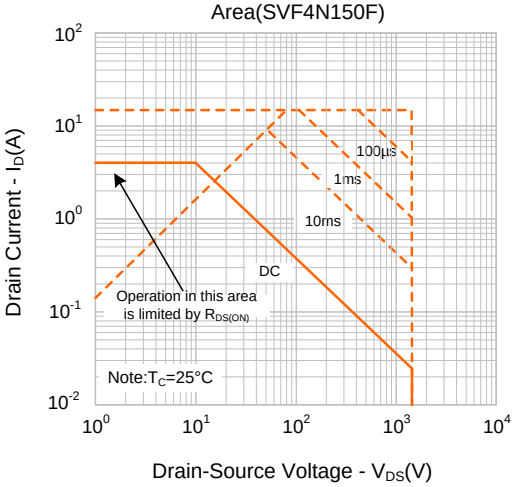


Figure 10-1. Transient Thermal Impedance(SVF4N150PF)

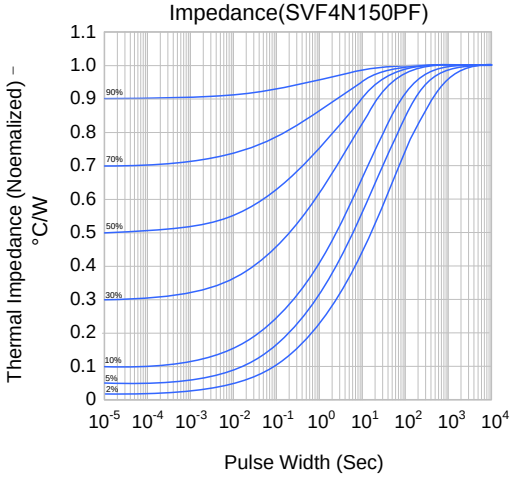


Figure 10-2. Transient Thermal Impedance(SVF4N150P7)

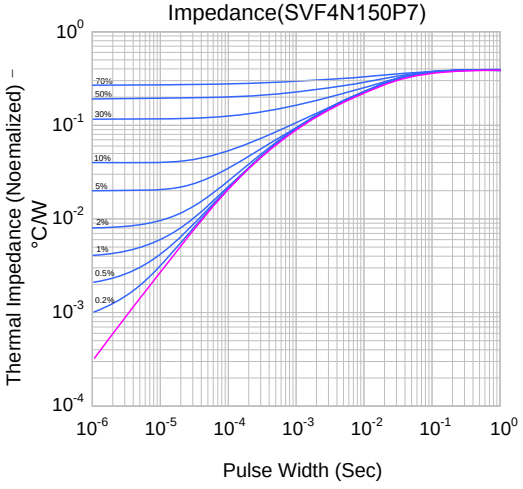
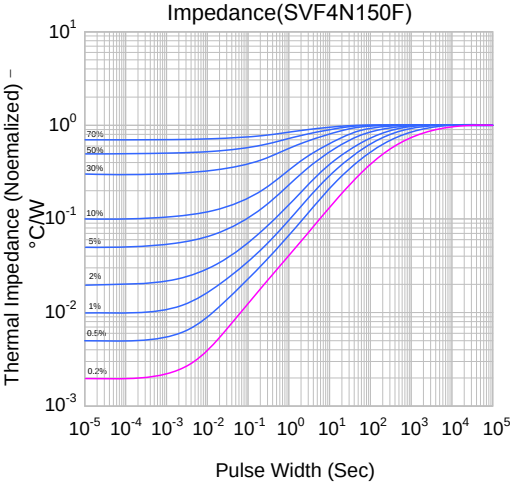
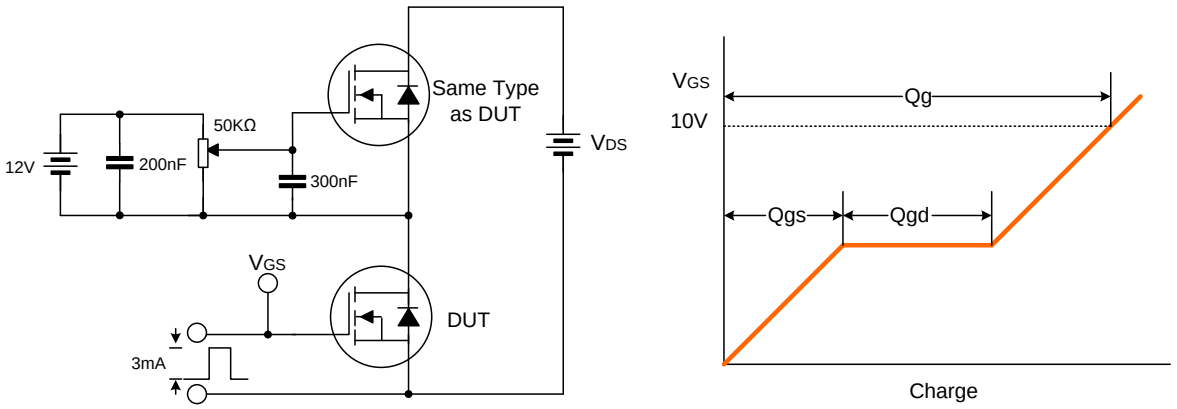


Figure 10-3. Transient Thermal Impedance(SVF4N150F)

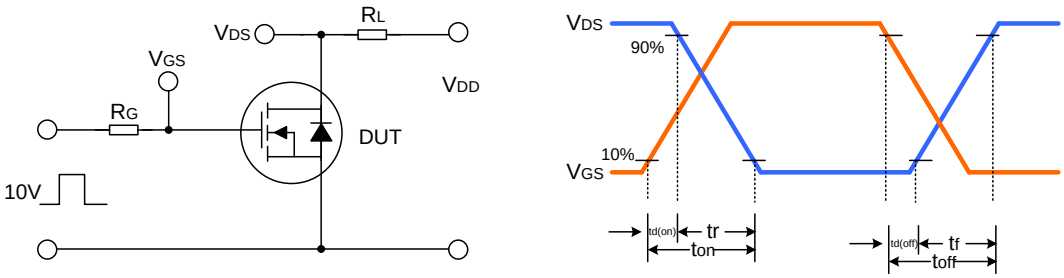


TYPICAL TEST CIRCUIT

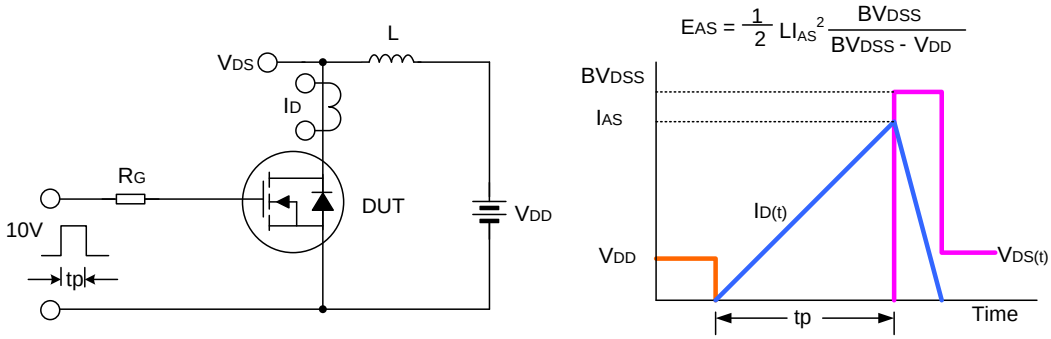
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



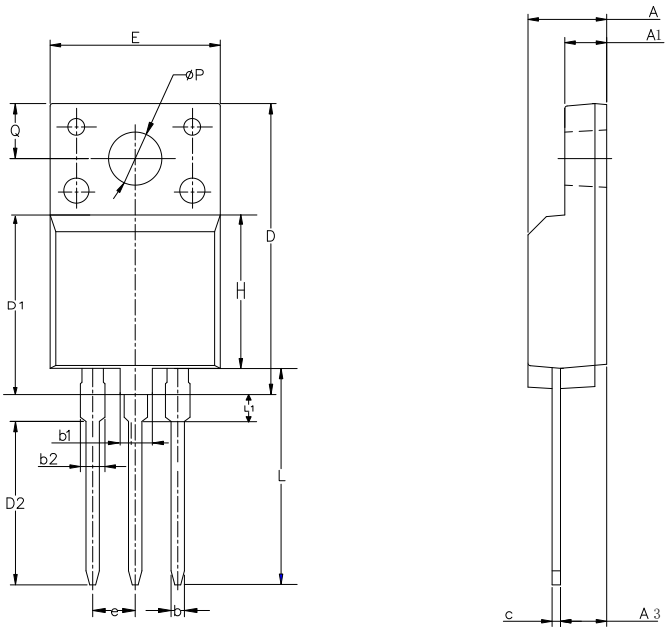
Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE

TO-3PF

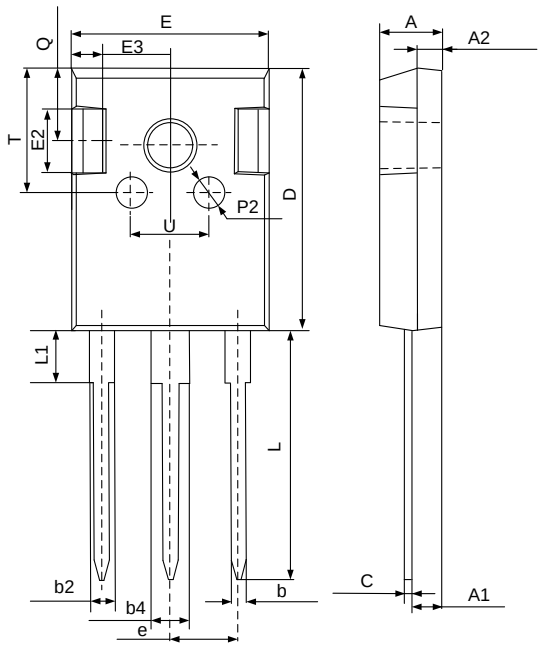
UNIT: mm



SYMBOL	MIN	NOM	MAX
A	5.30	5.56	5.70
A1	2.80	3.05	3.20
A3	3.10	3.25	3.50
b	0.65	0.82	0.95
b1	3.80	3.97	4.20
b2	1.80	2.05	2.20
c	0.80	0.93	1.10
D	26.30	26.38	26.70
D1	16.30	16.40	16.70
D2	14.60	14.89	15.00
E	15.30	15.34	15.70
e	5.15	5.45	5.75
H	14.30	14.40	14.70
L	18.90	19.35	19.70
L1	2.30	2.53	2.70
øP	3.40	3.63	3.80
Q	4.40	4.51	4.60

TO-247-3L

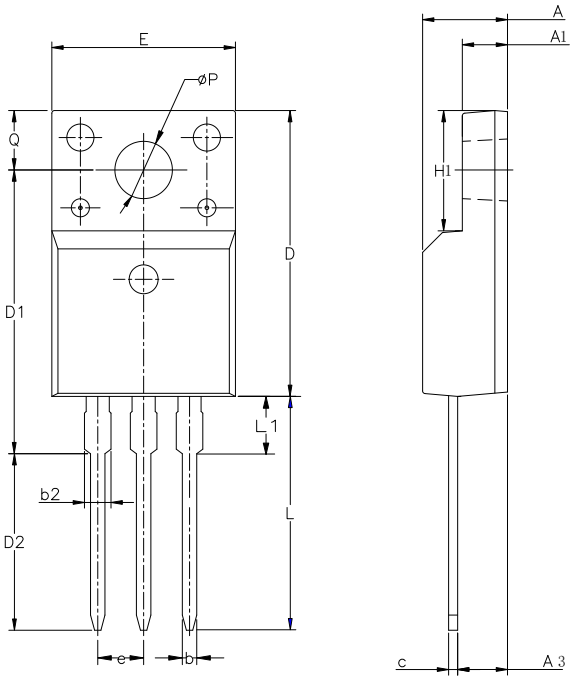
UNIT: mm



SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16	– – –	1.26
b2	1.95	– – –	2.15
b4	2.96	– – –	3.20
c	0.59	– – –	0.66
D	20.80	21.00	21.20
E	15.60	15.80	16.00
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e		5.44 BSC	
L	19.72	19.92	20.12
L1	– – –	– – –	4.30
P2	2.40	2.50	2.60
Q	5.60	5.80	6.00
T	9.80	10.00	10.20
U	6.00	6.20	6.40

PACKAGE OUTLINE

TO-220F-3L **UNIT: mm**



SYMBOL	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.70	0.80	0.90
b2	—	—	1.47
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	15.30	15.75	16.30
D2	9.30	9.80	10.30
E	9.73	10.16	10.36
e		2.54BSC	
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	/	/	3.50
øP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Part No.:	SVF4N150PF(P7)(F)	Document Type:	Datasheet
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Rev.: 1.3

Revision History:

1. Add the package outline of TO-220F-3L

Rev.: 1.2

Revision History:

1. Add the package outline of TO-247-3L

Rev.: 1.1

Revision History:

1. Modify the ID=6.5A to 2.0A of Fig.8:

Rev.: 1.0

Revision History:

1. First release